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Paramagnetic anisotropic magnetoresistance in thin films of $SrRuO_3$

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$SrRuO_3$ is an itinerant ferromagnet and in its thin film form when grown on miscut $SrTiO_3$ it has T_c of $\sim$ 150 K and strong uniaxial anisotropy. We measured both the Hall effect and the magnetoresistance (MR) of the films as a function of the angle between the applied field and the normal to the films at temperatures above T_c. We extracted the extraordinary Hall effect that is proportional to the perpendicular component of the magnetization and thus the MR for each angle of the applied field could be correlated with the magnitude and orientation of the induced magnetization. We successfully fit the MR data with a second order magnetization expansion, which indicates large anisotropic MR in the paramagnetic state. The extremum values of resistivity are not obtained for currents parallel or perpendicular to the magnetization, probably due to the crystal symmetry.

I. INTRODUCTION

The phenomenon of anisotropic magnetoresistance (AMR) in magnetic conductors expresses the dependence of the resistivity ρ on the angle δ between the current $\mathbf{J}$ and the magnetization $\mathbf{M}$. In polycrystals the AMR effect is commonly found to follow: $\rho = \rho_\perp + (\rho_\parallel - \rho_\perp)\cos^2\delta$ where $\rho_\perp$ is the resistivity when $\mathbf{J}\perp\mathbf{M}$, and $\rho_\parallel$ is the resistivity when $\mathbf{J}\parallel\mathbf{M}$ [1]. This simple relation is not expected to hold in crystalline samples where both the current orientation relative to the lattice as well as the magnetization orientation relative to the lattice play an important role.

Here we present AMR measurements of thin films of the $4d$ itinerant ferromagnet $SrRuO_3$ above T_c ($T_c \sim 150$ K). Those films are epitaxial and characterized by large uniaxial magnetocrystalline anisotropy (MCA) [2]. In our measurements, we study the AMR in uncommon conditions: (a) while in most AMR measurements the orientation of $\mathbf{M}$ is changed without changing its magnitude, here, because of the large MCA both orientation and magnitude of $\mathbf{M}$ are changing; and (b) while in most AMR measurement the applied field $\mathbf{H}$ is parallel to $\mathbf{M}$, here, because of the large MCA $\mathbf{M} \nparallel \mathbf{H}$ except for the cases where $\mathbf{H}$ is along the easy or hard axes. Therefore, to explore the AMR in $SrRuO_3$ it is not sufficient to measure magnetoresistance (MR) as a function of angle, but we need to independently determine both the magnitude and orientation of $\mathbf{M}$.

Our films are grown on miscut (2°) $SrTiO_3$ substrates using reactive electron beam epitaxy. The films have orthorhombic structure ($a = 5.53$ Å, $b = 5.57$ Å, $c = 7.85$ Å) and they grow uniformly (without twinning) with the c axis in the film plane and the a and b axes at 45° out of the plane (see Fig. 1) [3]. The MCA is uniaxial with the easy axis along the b axis and thus the uniform growth of the measured films can be confirmed by MR measurements in the ferromagnetic phase [4]. The films were patterned by photolithography to allow Hall effect (HE) and MR measurements. The sample whose results are presented here is 300 Å thick with $T_c \sim 147$ K and resistivity ratio of ~ 13.

II. MEASUREMENTS AND DISCUSSION

Our measurements have two parts: (a) extraordinary Hall effect (EHE) [5] measurements from which we extract both the magnitude and the orientation of $\mathbf{M}$, and (b) MR measurements for currents in the [001] and [1$\bar{1}$0] directions. Combining the two measurements we show that the MR can be fit very well with a second order magnetization expansion.

Both HE and MR measurements were performed as a function of the angle ϕ between the applied field $\mathbf{H}$ and the easy axis, where $\mathbf{H}$ is rotating in the (001) plane. Each film has two kinds of patterns: a pattern with current along the [1$\bar{1}$0] direction (denoted P_{ab}) and a pattern with current along the [001] direction (denoted P_c). While in P_{ab} the angle between $\mathbf{J}$ and $\mathbf{H}$ varies with ϕ, in P_c the field $\mathbf{H}$ is always perpendicular to $\mathbf{J}$. The measurement configuration is illustrated in Fig. 1.

The Hall field in magnetic conductors has two contributions:

$$\mathbf{E}_H = -R_0\mathbf{J}\times\mathbf{B} - R_s\mathbf{J}\times\mu_0\mathbf{M}$$

where $\mathbf{B}$ is the magnetic field, and R_0 and R_s are the ordinary and the extraordinary Hall coefficients, respectively. By measuring the HE in our films at a temperature where R_s vanishes [6] we determined R_0, which enabled to extract $\mu_0 R_s M_\perp$ (where $M_\perp$ is the component of $\mathbf{M}$ which is perpendicular to the film plane) at all temperatures. This is not sufficient, however, since we need to determine both components of $\mathbf{M}$. For that

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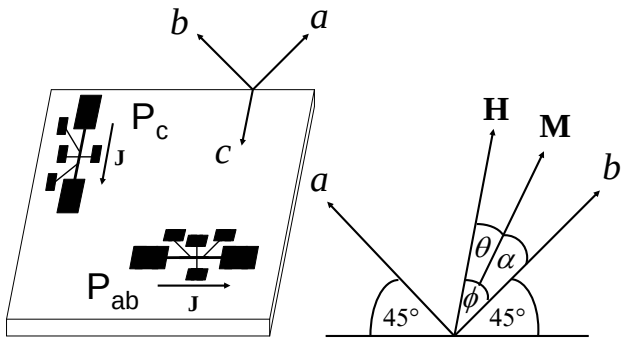


FIG. 1: A sketch of the patterned film. In pattern P_c the current **J** is in the [001] direction. In pattern P_{ab} the current **J** is in the $[1\bar{1}0]$ direction. The crystallographic directions b (easy axis), and a (hard axis) are at 45° out of the plane of the film. In our measurements the field **H** is rotating in the (001) plane, ϕ is the angle between **H** and b, α is the angle between the induced **M** and b, and θ is the angle between **M** and **H**.

we note that based on symmetry considerations we may assume that if a field **H**, that is applied in the (001) plane at an angle ϕ relative to the easy axis, creates a magnetization **M** pointing at an angle α relative to the easy axis, then applying the same field at an angle $-\phi$ will create the same magnetization, but at an angle $-\alpha$ [7]. In our case the easy axis is at 45° out of the plane thus symmetry considerations yield that $M_{\parallel}(\phi) = M_{\perp}(-\phi)$ where $M_{\parallel}$ and $M_{\perp}$ are the in-plane and perpendicular components of **M**, respectively. Consequently, by measuring the Hall resistivity (ρ_{EHE}) at ϕ and $-\phi$ we obtain: $\rho_{EHE}(\phi) = \mu_0 R_s M_{\perp}(\phi)$ and $\rho_{EHE}(-\phi) = \mu_0 R_s M_{\parallel}(\phi)$, which allows to determine **M** (multiplied by $\mu_0 R_s$). Figures 2a and 2b show the change in the magnitude and direction of **M** as a function of ϕ at $T = 170$ K determined with that method. As expected, **M** obtains its maximum value at $\phi = 0$ and lags behind **H** except for **H** along a and b. It seems that this is the first time that EHE which is sensitive only to the perpendicular component of the magnetization is used for extracting the full magnetization vector based on symmetry consideration. This is possible only due to the tilted easy axis. Where the easy axis is perpendicular or parallel to the film this scheme is not applicable.

Figures 2(c) and 2(d) present the MR measured at $T = 170$ K for $H = 6$ T and 8 T in P_{ab} and P_c. To fit the MR data we expand MR in **M**, noting that due to the MR symmetry under field inversion the lowest order expansion is of second order. Since in our experiment **M** remains in the (001) plane it is sufficient to use two components of **M**. We use the freedom of choosing the principle axes to take them in the crystallographic directions of a and b. Therefore, the general expansion of the

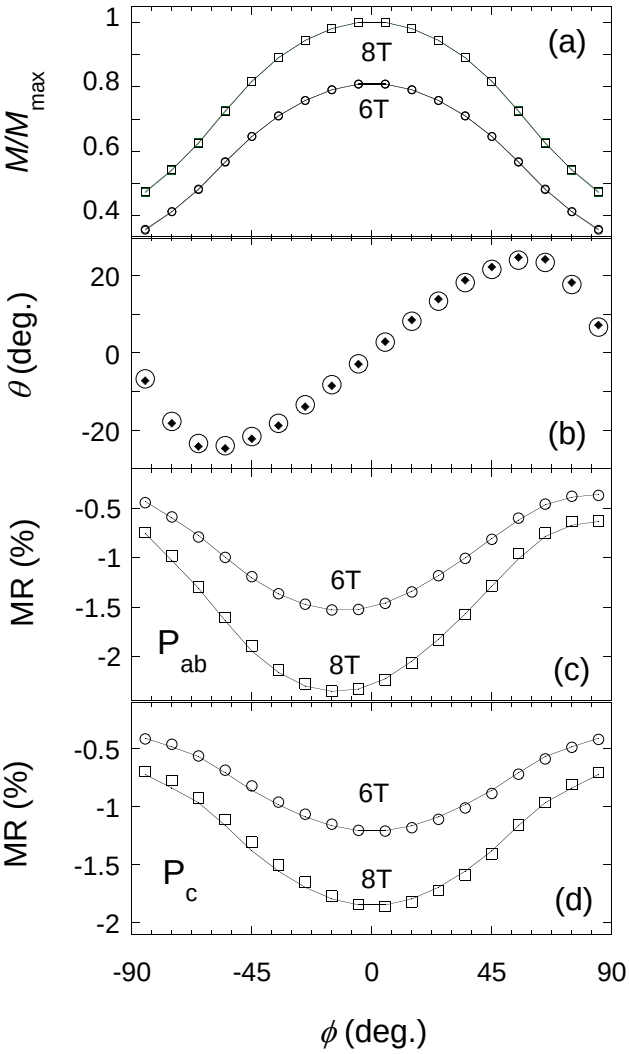


FIG. 2: Magnetization and MR data at 170 K as a function of the angle ϕ between **H** and the easy axis b, and fits of the MR data based on the measured **M** and Eq. 1. (a) The magnitude of **M** relative to $M_{\max}$, which is the magnitude of **M** obtained with $H = 8$ T applied along the easy axis. (b) The angle between **M** and **H** for $H = 8$ T (empty circles) and $H = 6$ T (full diamonds). (c) MR in P_{ab}. (d) MR in P_c. For graphs (c) and (d) the points represent the experimental results and the lines represent the fit.

MR to lowest order is:

$$MR = (\rho(H) - \rho(0))/\rho(0) = A(M_b^2 + \beta M_a^2 + \gamma M_b M_a) \quad (1)$$

where M_b and M_a are the components of **M** along the easy axis (b) and hard axis (a), respectively. The lines in Figs. 2(c) and 2(d) are fits of the MR data based on the measured **M** and Eq. 1.

We obtained the following fitting parameters at $T = 170$ K: $\beta = 1.4 \pm 0.2$, $\gamma = -0.6 \pm 0.1$ for the P_{ab} pattern, and $\beta = 1.7 \pm 0.2$, $\gamma = -0.1 \pm 0.1$ for the P_c pattern. The error limits indicate the evaluated changes in the

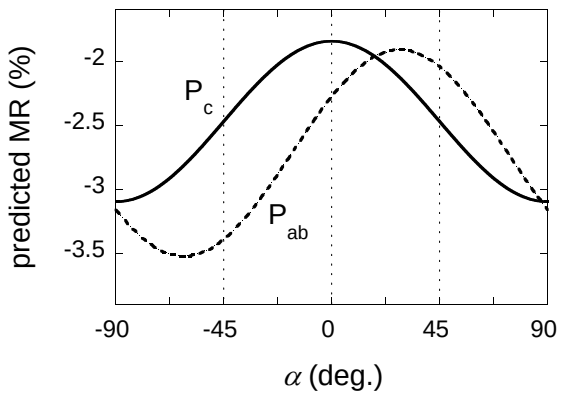


FIG. 3: The expected MR at 170 K and $H = 8$ T as a function of the angle α between $\mathbf{M}$ and b, assuming M is constant, for P_c (solid curve), and P_{ab} (dashed curve).

fitting parameters in case there is difference between the instrumental ϕ and the actual ϕ of up to 2°.

The fits of the MR data based on Eq. 1 allow us to determine the "clean" AMR effect; namely, how would the resistivity change if we could rotate $\mathbf{M}$ in the (001) plane without changing its magnitude. Figure 3 shows the expected behavior at $T = 170$ K for P_{ab} and P_c for a value of magnetization obtained with $H = 8$ T along the easy axis.

For P_c we note that although $\mathbf{J} \perp \mathbf{M}$ there is a significant AMR ($\beta \neq 1$), and that $\gamma = 0$ is within our experimental accuracy, as could be expected from symmetry considerations. These results exhibit strong dependence of the MR not only on the angle between $\mathbf{M}$ and $\mathbf{J}$ (which remains constant) but also on the direction of $\mathbf{M}$ relative to the crystal. For P_{ab} we note that the extremum values are not obtained for $\mathbf{J} \parallel \mathbf{M}$ or $\mathbf{J} \perp \mathbf{M}$ but at intermediate angles. In fact, the extremum values for P_{ab} are in between those obtained in P_c (along the a and b axes) and those observed in polycrystals (parallel and perpendicular to $\mathbf{J}$). This shows that in our case the AMR related to the orientation of $\mathbf{M}$ with respect to the lattice is of the same order of magnitude as the AMR due to the relative orientation of $\mathbf{M}$ and $\mathbf{J}$. We also note that for $\alpha = 45°$, which corresponds to $\mathbf{M}$ perpendicular to the plane the MR is different in P_{ab} and P_c despite the fact that in both cases $\mathbf{J} \perp \mathbf{M}$. This illustrates the dependence of MR on the direction of $\mathbf{J}$ relative to the crystal.

In conclusion, we have presented AMR investigation of $SrRuO_3$ with simultaneous measurements of $\mathbf{M}$ and MR in the same pattern thus enabling accurate determination of its AMR behavior despite the change in the magnitude of $\mathbf{M}$ and in its relative angle with $\mathbf{H}$. The results indicate significant AMR even in the paramagnetic state, where $\mathbf{M}$ is relatively small, and large effect of the orientation of $\mathbf{M}$ and $\mathbf{J}$ relative to the crystal axes.

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[4] As the sample is rotated in applied magnetic field, jumps in magnetoresistance which correspond to magnetization reversal occur at angles consistent with a uniform direction of the easy axis throughout the sample.
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